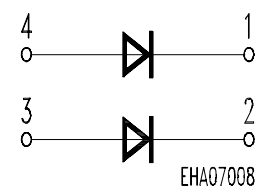
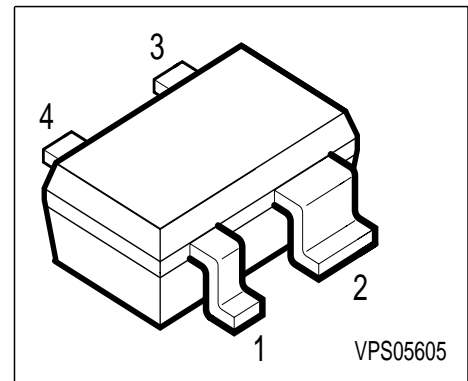


### Silicon Schottky Diodes

- For low-loss, fast-recovery, meter protection, bias isolation and clamping applications
- Integrated diffused guard ring
- Low forward voltage



**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Ordering Code	Pin Configuration				Package
BAT 64-07W	67s	Q62702-A3470	1 = C1	2 = C2	3 = A2	4 = A1	SOT-343

### Maximum Ratings

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	40	V
Forward current	$I_F$	250	mA
Average forward current (50/60Hz, sinus)	$I_{FAV}$	120	
Surge forward current ( $t < 100\mu s$ )	$I_{FSM}$	800	
Total power dissipation, $T_S \leq 104\text{ }^\circ\text{C}$	$P_{tot}$	250	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55...+150	

### Thermal Resistance

Junction - ambient <sup>1)</sup>	$R_{thJA}$	$\leq 455$	K/W
Junction - soldering point	$R_{thJS}$	$\leq 185$	

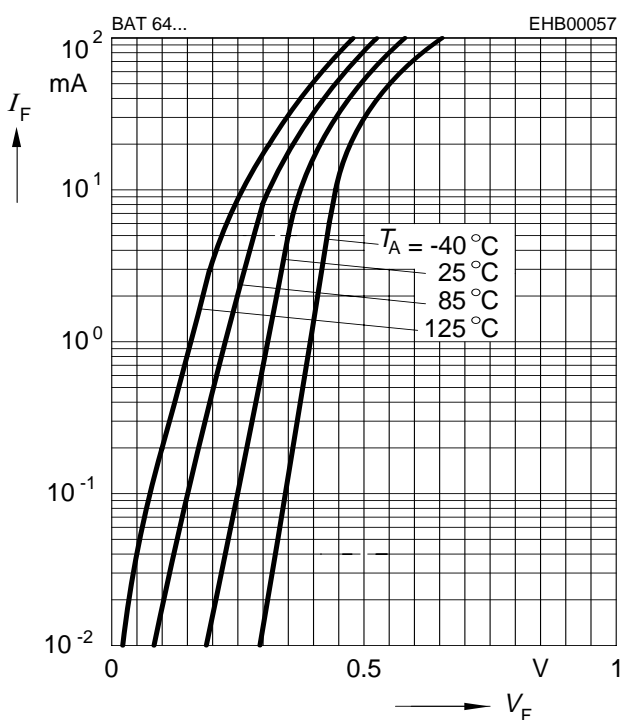
1) Package mounted on epoxy pcb 40mm x 40mm x 1.5mm / 6cm<sup>2</sup> Cu

Electrical Characteristics at  $T_A = 25\text{ °C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC characteristics</b>					
Reverse current $V_R = 30\text{ V}$	$I_R$	-	-	2	$\mu\text{A}$
Reverse current $V_R = 30\text{ V}, T_A = 85\text{ °C}$	$I_R$	-	-	200	
Forward voltage $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$ $I_F = 30\text{ mA}$ $I_F = 100\text{ mA}$	$V_F$	-	320 385 440 570	350 430 520 750	mV
<b>AC characteristics</b>					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$	$C_T$	-	4	6	pF

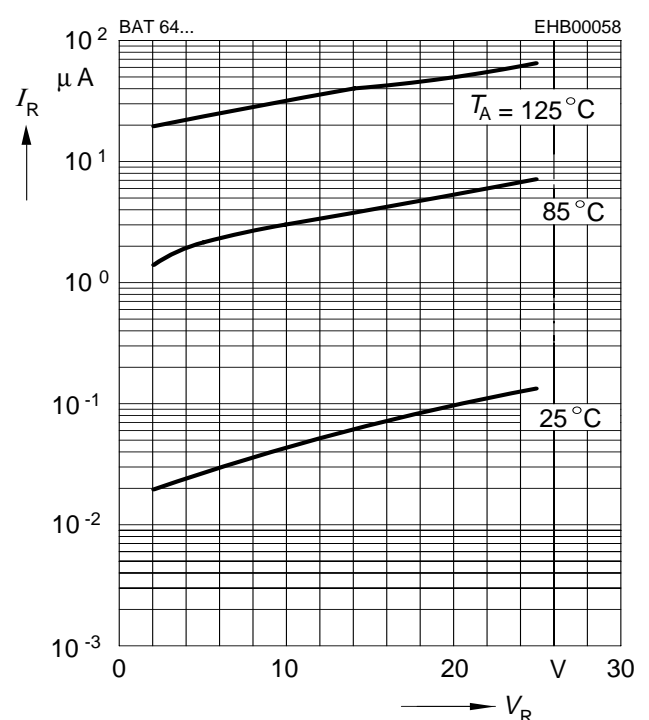
**Forward current**  $I_F = f(V_F)$

$T_A = \text{Parameter}$



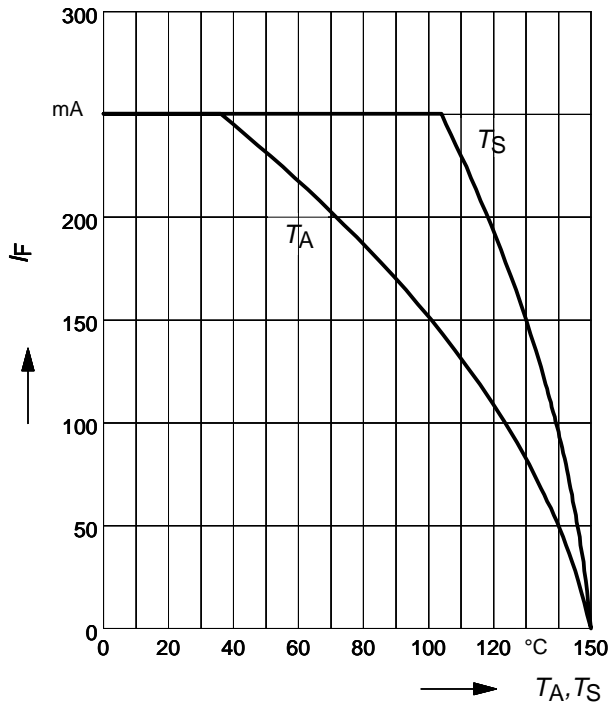
**Reverse current**  $I_R = f(V_R)$

$T_A = \text{Parameter}$

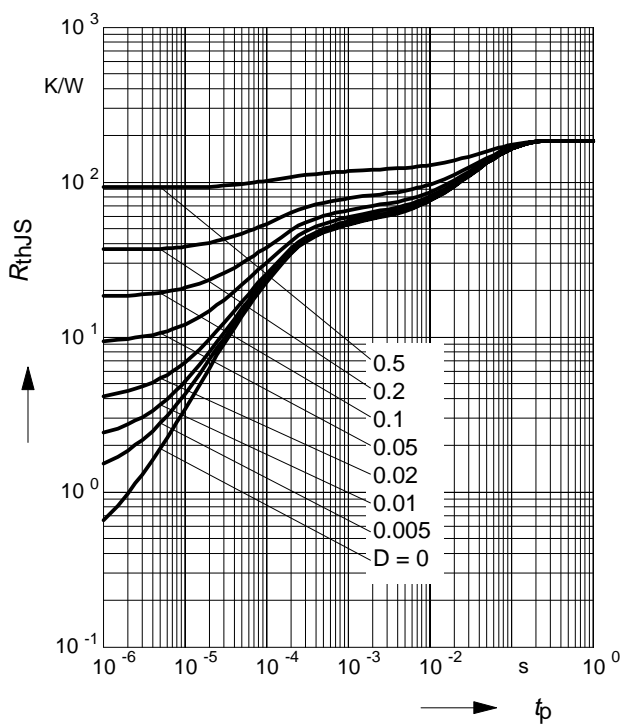


Forward current  $I_F = f(T_A^*; T_S)$

\* Package mounted on epoxy



Permissible Pulse Load  $R_{THJS} = f(t_p)$



Permissible Pulse Load  $I_{Fmax}/I_{FDC} = f(t_p)$

